

110 Watts - 50 Volts, 330µs, 10% Radar 1200 - 1400 MHz

<b>GENERAL DESCRIPTION</b> The 1214-110M is an internally matched, COMMON BASE transistor capable of providing 110 Watts of pulsed RF output power at 330 µs pulse width, 10% duty factor across the band 1200 to 1400 MHz. This hermetically solder-sealed transistor is specifically designed for L-Band radar applications. It utilizes gold metallization and diffused emitter ballasting to provide high reliability and supreme ruggedness.			CASE OUTLINE 55KT, STYLE 1
ABSOL	UTE MAXIMUM RATIN	IGS	<u> </u>
Maximum Power Dissipation @ 25°C		270 Watts	
Maximum	Voltage and Current		
BVces	Collector to Emitter Voltage	75 Volts	
BVebo	Emitter to Base Voltage	3.0 Volts	
Ic	Collector Current	8 Amps	
Maximum	Temperatures		
Storage Temperature		$-65 \text{ to} + 200^{\circ} \text{C}$	
Operating Junction Temperature		$+200^{\circ}C$	
- 0	-		

## ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
Pout Pg ηc Rl Droop Flatness VSWR <sup>1</sup> VSWRs	Power Out Power Gain Collector Efficiency Input Return loss Droop Flatness Load Mismatch Tolerance Load Mismatch - Stability	Freq = 1200 – 1400 MHz Vcc = 50 Volts Pin = 20 Watts Pulse Width = 330µs Duty Factor = 10%	110 7.4 50 10	55	0.5 1.25 3:1 1.5:1	Watts dB % dB dB dB

#### FUNCTIONAL CHARACTERISTICS @ 25°C

Bvces Ices θjc <sup>1</sup>	Collector to Emitter Breakdown Collector to Emitter Leakage Thermal Resistance	Ic = 100 mA Vce = 50 Volts Rated Pulse Condition	75		10 0.65	Volts mA °C/W
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## Performance Curves





### **Impedance Information**



Frequencies (MHz)	$Z_{Source}(\Omega)$	$Z_{Load}(\Omega)^{2}$
1200	3.36-j3.12	4.97+j0.15
1300	3.5-j2.4	5.33-j2.86
1400	3.81-j1.3	2.88-j3.86

Note 2:  $Z_{Load}$  exclusive of bias circuit

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#### **Test Circuit**



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